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Kişisel Bilgiler

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Publons / Web Of Science ResearcherID: HOF-0504-2023

Yabancı Diller

İngilizce, B2 Orta Üstü

Yaptığı Tezler

Yüksek Lisans, Yarı-kesikli bir stiren polimerizasyon reaktörünün bulanık kontrol yöntemi ile sıcaklık kontrolü, Gazi Üniversitesi, Fen Bilimleri Enstitüsü, 2009

SCI, SSCI ve AHCI İndekslerine Giren Dergilerde Yayınlanan Makaleler

I. **The probe of current conduction mechanisms, interface states, and the forward bias intersection point of the al/Al2O3/Ge/p-Si heterostructures depending on temperature**
Akın B., A.Hameed S., ALTINDAL YERİŞKİN S., ULUSOY M., Durmuş H.
Materials Science in Semiconductor Processing, cilt.184, 2024 (SCI-Expanded)

II. **Frequency-dependent dielectric, electric modulus, and ac conductivity features of Au/n-Si Schottky diodes (SDs) with PVC and (PVC:Graphite/Graphene-Oxide) interlayer**
ALTINDAL YERİŞKİN S., Taşçıoğlu İ., BADALI Y.
Journal of Physics D: Applied Physics, cilt.57, sa.31, 2024 (SCI-Expanded)

III. **The Electrical and Photodetector Characteristics of the Graphene:PVA/p-Si Schottky Structures Depending on Illumination Intensities**
ULUSOY M., Koçyiğit S., TATAROĞLU A., ALTINDAL YERİŞKİN S.
ACS Omega, cilt.9, sa.29, ss.32243-32255, 2024 (SCI-Expanded)

IV. **Quaternary functional semiconductor devices**
ALTINDAL YERİŞKİN S., Dere A., Orman Y., Yakuphanoğlu F.
Physica Scripta, cilt.99, sa.7, 2024 (SCI-Expanded)

V. **Origin of frequency and voltage dependent negative dielectric properties in the Al/p-Si Schottky diodes with (Cd0.3Zn0.7O) interfacial layer in the wide range of frequency and voltage**
Delen N., Altındal Yerişkin S., ÖZBAY A., Taşçıoğlu İ.
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VI. **Examination on the current conduction mechanisms of Au/n-Si diodes with ZnO–PVP and ZnO/Ag2WO4 –PVP interfacial layers**
Taşçıoğlu I., Pirgholi-Givi G., Yerişkin S., AZIZIAN-KALANDARAGH Y.
Journal of Sol-Gel Science and Technology, cilt.107, sa.3, ss.536-547, 2023 (SCI-Expanded)

VII. **Analysis of the Current Transport Characteristics (CTCs) in the Au/n-Si Schottky Diodes (SDs) with Al2O3Interfacial Layer over Wide Temperature Range**
Buyukbas-Ulusan A., TATAROĞLU A., Altlndal-Yerişkin S.
ECS Journal of Solid State Science and Technology, cilt.12, sa.8, 2023 (SCI-Expanded)

VIII. **Analysis of the Current Transport Characteristics (CTCs) in the Au/n-Si Schottky Diodes (SDs) with Al2O3 Interfacial Layer over Wide Temperature Range**
Buyukbas-Ulusan A., Tataroğlu A., Altındal Yerişkin S.
ECS JOURNAL OF SOLID STATE SCIENCE AND TECHNOLOGY, cilt.12, ss.83010, 2023 (SCI-Expanded)

IX. **Dielectric properties of MS diodes with Ag:ZnO doped PVP interfacial layer depending on voltage and frequency**
Altındal Yerişkin S., ERBİLEN TANRIKULU E., ULUSOY M.
Materials Chemistry and Physics, cilt.303, 2023 (SCI-Expanded)

X. **Analysis of admittance measurements of Al/Gr-PVA/p-Si (MPS) structure**
Ata D., Yeriskin S., Tataroglu A., Balbasi M.
JOURNAL OF PHYSICS AND CHEMISTRY OF SOLIDS, cilt.169, 2022 (SCI-Expanded)

XI. **On the changes in the dielectric, electric modulus, and ac electrical-conductivity in the Al/(C(29)H(32)O17)/p-Si (MPS) structures in wide range of frequency and voltage**
ERBİLEN TANRIKULU E., Yeriskin S.
PHYSICA B-CONDENSED MATTER, cilt.623, 2021 (SCI-Expanded)

XII. **Electrical parameters of Au/(%1Ni-PVA)/n-Si (MPS) structure: Surface states and their lifetimes**
Cetinkaya H. G., Demirezen S., Yeriskin S.
PHYSICA B-CONDENSED MATTER, cilt.621, 2021 (SCI-Expanded)

XIII. **Frequency and voltage-dependent dielectric spectroscopy characterization of Al/(Coumarin-PVA)/p-Si structures**
DEMİREZEN S., Yeriskin S.
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, cilt.32, sa.20, ss.25339-25349, 2021 (SCI-Expanded)

XIV. **Influence of graphene doping rate in PVA organic thin film on the performance of Al/p-Si structure**
Yeriskin S., ŞAFAK ASAR Y.
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, cilt.32, sa.18, ss.22860-22867, 2021 (SCI-Expanded)

XV. **Complex dielectric, complex electric modulus, and electrical conductivity in Al/(Graphene-PVA)/p-Si (metal-polymer-semiconductor) structures**
Karadas S., Yeriskin S., BALBAŞI M., Azizian-Kalandaragh Y.
Journal of Physics and Chemistry of Solids, cilt.148, 2021 (SCI-Expanded)

XVI. **Illumination Dependent Electrical Data Identification of the CdZnO Interlayered Metal-Semiconductor Structures**
Tan S. O., Tascioglu I., Altindal Yeriskin S., Tecimer H., Yakuphanoglu F.
SILICON, sa.12, ss.2885-2891, 2020 (SCI-Expanded)

XVII. **Dielectric, ac conductivity and electric modulus studies at MPS structure with (Cu₂O-CuO)-doped PVA interfacial layer**
Buyukbas-Ulusan A., Yeriskin S., Tataroglu A., Balbasi M., Azizian-Kalandaragh Y.
OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, sa.5-6, ss.256-260, 2020 (SCI-Expanded)

XVIII. **A detailed comparative study on electrical and photovoltaic characteristics of Al/p-Si photodiodes with coumarin-doped PVA interfacial layer: the effect of doping concentration**
DEMİREZEN S., Altindal Yeriskin S.
POLYMER BULLETIN, cilt.77, sa.1, ss.49-71, 2020 (SCI-Expanded)

XIX. **The effects of (graphene doped-PVA) interlayer on the determinative electrical parameters of the Au/n-Si (MS) structures at room temperature**
Yeriskin S., BALBAŞI M., Orak I.

JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, sa.18, ss.14040-14048, 2017 (SCI-Expanded)

XX. **Temperature and voltage dependence of barrier height and ideality factor in Au/0.07 graphene-doped PVA/n-Si structures**
Yeriskin S., Balbasi M., Demirezen S.
INDIAN JOURNAL OF PHYSICS, sa.4, ss.421-430, 2017 (SCI-Expanded)

XXI. **Frequency and voltage dependence of dielectric properties, complex electric modulus, and electrical conductivity in Au/7% graphene doped-PVA/n-Si (MPS) structures**
Yeriskin S., BALBAŞI M., TATAROĞLU A.
JOURNAL OF APPLIED POLYMER SCIENCE, sa.33, 2016 (SCI-Expanded)

XXII. **The investigation of dielectric properties and ac conductivity of Au/GO-doped PrBaCoO nanoceramic/n-Si capacitors using impedance spectroscopy method**
Kaya A., Alialy S., Demirezen S., Balbasi M., Yeriskin S., Aytimur A.
CERAMICS INTERNATIONAL, sa.2, ss.3322-3329, 2016 (SCI-Expanded)

XXIII. **Frequency and voltage dependent profile of dielectric properties, electric modulus and ac electrical conductivity in the PrBaCoO nanofiber capacitors**
Demirezen S., Kaya A., Yeriskin S., Balbasi M., Uslu I.
Results in Physics, ss.180-185, 2016 (SCI-Expanded)

XXIV. **Electrical and Dielectric Characteristics of Al/Polyindole Schottky Barrier Diodes. II. Frequency Dependence**
Yeriskin S., ÜNAL H. İ., SARI B.
JOURNAL OF APPLIED POLYMER SCIENCE, sa.1, ss.390-396, 2011 (SCI-Expanded)

Diğer Dergilerde Yayınlanan Makaleler

I. **On the Voltage Dependent Series Resistance, Interface Traps, and Conduction Mechanisms in the Al/(Ti-doped DLC)/p-Si/Au Schottky Barrier Diodes (SBDs)**
hameed s., BERKÜN Ö., Altındal Yerişkin S.
Gazi University Journal of Science Part A: Engineering and Innovation, cilt.11, sa.1, ss.235-244, 2024 (Hakemli Dergi)

II. **Voltage Dependent Profiles of the Surface States and Series Resistance (Rs) in the Al-(Cd:ZnO)-pSi Schottky Diodes (SDs) Utilizing Voltage-Current (IV) Characteristics**
Delen N., Tascioglu I., ALTINDAL YERİŞKİN S., ÖZBAY A.
Gazi University Journal of Science, cilt.37, sa.1, ss.457-463, 2024 (ESCI)

Metrikler

Yayın: 27
Atıf (WoS): 612
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Akademi Dışı Deneyim

ÇEVRE VE ŞEHİRCİLİK BAKANLIĞI
GÜLHANE ASKERİ TIP AKADEMİSİ KOMUTANLIĞI